

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5168	((("semiconductor memory" and "memory cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))) and (sense adj4 amplifier)) and row and column and array.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:20
L2	7	((("semiconductor memory" and "memory cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))) and (sense adj4 amplifier)) and row and column and array) and sub\$1decoder and gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:21
L3	24	((DRAM or (dynamic adj5 random adj5 access adj6 memory)) and PMOS and NMOS and "memory cell array") and transistor and well) and sub\$1decoder	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:21
L4	82	((("semiconductor memory" and "memory cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))) and (sense adj4 amplifier)) and row and column and array) and (sub\$1decoder or pre\$1decoder)) and 365/63.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:21
L5	29	(("semiconductor memory" near5 "memory cell") near5 (DRAM or (dynamic adj5 random adj5 access adj5 memory))) near11 amplifier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:22
L6	76	(("memory cell" same row same column) same substrat\$2) same amplifier same "memory array"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:22
L7	12	"sense amplifier driver" and subdecod\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:22
L8	57	(("sense amplifier driver" and decod\$3) and gap and row and column) and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:23

L9	45	((("sense amplifier driver" and decod\$3) and gap and row and column) and memory) and "365"/\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:23
S1	41267	"semiconductor memory" and "memory cell"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:35
S2	97088	DRAM or (dynamic adj5 random adj5 access adj5 memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:04
S3	13849	("semiconductor memory" and "memory cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:04
S4	6757	(("semiconductor memory" and "memory cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))) and (sense adj3 amplifier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:05
S5	4822	((("semiconductor memory" and "memory cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))) and (sense adj3 amplifier)) and row and column and array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:20
S6	4	(((("semiconductor memory" and "memory cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))) and (sense adj3 amplifier)) and row and column and array) and sub\$1decoder and gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:21
S7	1828	(DRAM or (dynamic adj5 random adj5 access adj5 memory)) and PMOS and NMOS and "memory cell array"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:08
S8	1259	((DRAM or (dynamic adj5 random adj5 access adj5 memory)) and PMOS and NMOS and "memory cell array") and transistor and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:09

S9	21	((DRAM or (dynamic adj5 random adj5 access adj5 memory)) and PMOS and NMOS and "memory cell array") and transistor and well) and sub\$1decoder	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:21
S10	790	((("semiconductor memory" and "memory cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))) and (sense adj3 amplifier)) and row and column and array) and (sub\$1decoder or pre\$1decoder)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:15
S11	684	(((("semiconductor memory" and "memory cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))) and (sense adj3 amplifier)) and row and column and array) and (sub\$1decoder or pre\$1decoder)) and "365"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:33
S12	79	(((("semiconductor memory" and "memory cell") and (DRAM or (dynamic adj5 random adj5 access adj5 memory))) and (sense adj3 amplifier)) and row and column and array) and (sub\$1decoder or pre\$1decoder)) and 365/63.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:21
S13	15711	"semiconductor memory" near5 "memory cell"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:35
S14	819	("semiconductor memory" near5 "memory cell") near5 (DRAM or (dynamic adj5 random adj5 access adj5 memory))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:51
S15	23	(("semiconductor memory" near5 "memory cell") near5 (DRAM or (dynamic adj5 random adj5 access adj5 memory))) near10 amplifier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:22
S16	23578	"memory cell" same row same column	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:38
S17	2366	("memory cell" same row same column) same substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:39

S18	67	(("memory cell" same row same column) same substrate) same amplifier same "memory array"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:22
S19	2	(("memory cell" same row same column) same substrate) same amplifier same sub\$1decoder	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:55
S20	450	"sense amplifier driver"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:53
S21	9	"sense amplifier driver" and subdecoder	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:22
S22	15	subdecoder near5 amplifier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:56
S23	283	"sense amplifier driver" and decoder	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:57
S24	53	("sense amplifier driver" and decoder) and gap and row and column	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 16:58
S25	53	(("sense amplifier driver" and decoder) and gap and row and column) and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:22
S26	41	((("sense amplifier driver" and decoder) and gap and row and column) and memory) and "365"/\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 06:23
S27	123	kawasaki-satoshi.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 17:08

S28	1	kawasaki-satoshi-\$in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/07 17:09
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